Supplementary Information

Controlling the threshold voltage of β-Ga₂O₃ field-effect transistors via remote fluorine plasma treatment

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**Figure S1** Height profile of pristine and fluorinated $\beta$-Ga$_2$O$_3$ flakes.
Figure S2 (a) $I_{DS}$–$V_{DS}$ output and (b) transfer characteristics of back-gated $\beta$-$\text{Ga}_2\text{O}_3$ MOSFETs before and after the CF$_4$ plasma treatment.
Figure S3 $I_D^{1/2}$ vs $V_{GS}$ output characteristics of the pristine and fluorinated $\beta$-$\text{Ga}_2\text{O}_3$ MISFETs.